

KSA733

Low Frequency Amplifier

- Collector-Base Voltage : V_{CBO}= -60V
- Complement to KSC945
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|------------------|-----------------------------|-----------|-------|
| V _{CBO} | Collector-Base Voltage | -60 | V |
| V _{CEO} | Collector-Emitter Voltage | -50 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| c | Collector Current | -150 | mA |
| P _C | Collector Power Dissipation | 250 | mW |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -55 ~ 150 | °C |

Electrical Characteristics T_a =25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|-------|-------|-------|-------|
| BV _{CBO} | Collector-Base Breakdown Voltage | I _C = -100μA, I _E =0 | -60 | | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C = -10mA. I _B =0 | -50 | | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_E = -10\mu A. I_C = 0$ | - 5 | | | V |
| I _{CBO} | Collector Cut-off Current | V _{CB} =60V, I _E =0 | | | -100 | nA |
| I _{EBO} | Emitter Cut-off Current | V _{EB} = -5V, I _C =0 | | | -100 | nA |
| h _{FE} | DC Current Gain | V_{CE} = -6V, I_{C} = -1mA | 40 | | 700 | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = -100mA, I _B = -10mA | | -0.18 | -0.3 | V |
| V _{BE} (on) | Base-Emitter On Voltage | V_{CE} = -6V, I_{C} = -1mA | -0.50 | -0.62 | -0.80 | V |
| f _T | Current Gain Bandwidth Product | $V_{CE} = -6V, I_{C} = -10mA$ | 50 | 180 | | MHz |
| C _{ob} | Output Capacitance | $V_{CB} = -10V, I_{E} = 0, f = 1MHz$ | | 2.8 | | pF |
| NF | Noise Figure | V_{CE} = -6V, I_{C} = -0.3mA f=1MHz, Rs=10k Ω | | 6.0 | 20 | dB |

h_{FE} Classification

| Classification | R | 0 | Υ | G | L |
|-----------------|---------|----------|-----------|-----------|-----------|
| h _{FE} | 40 ~ 80 | 70 ~ 140 | 120 ~ 240 | 200 ~ 400 | 350 ~ 700 |

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Typical Characteristics

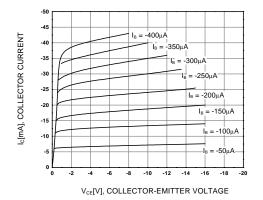


Figure 1. Static Characteristic

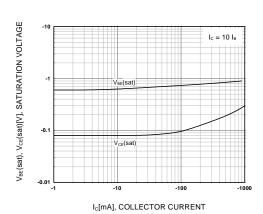


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

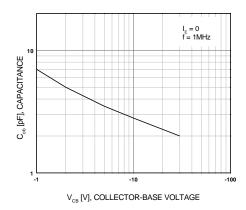


Figure 5. Collector Output Capacitance

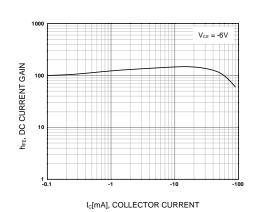


Figure 2. DC current Gain

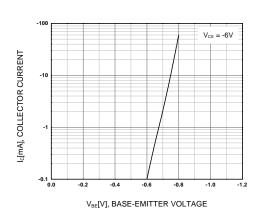


Figure 4. Base-Emitter On Voltage

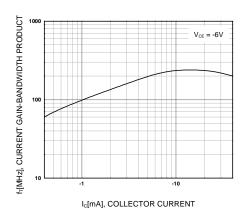
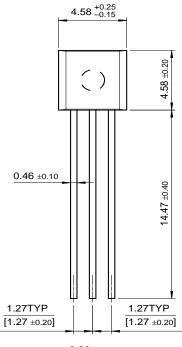


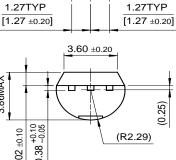
Figure 6. Current Gain Bandwidth Product

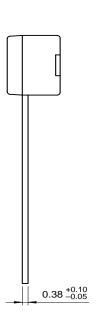
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Dimensions in Millimeters

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